

TO-220-3L Plastic-Encapsulate Transistors

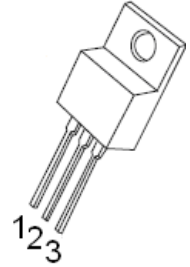
2SD2137A TRANSISTOR (NPN)

FEATURES

- High DC Current Gain
- Low Collector to Emitter Saturation Voltage $V_{CE(sat)}$
- Allowing Automatic Insertion with Radial Taping

TO-220-3L

1. BASE
2. COLLECTOR
3. EMITTER



MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	80	V
V_{CEO}	Collector-Emitter Voltage	80	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current	3	A
P_C	Collector Power Dissipation	2	W
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	63	$^\circ\text{C/W}$
T_j	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55~+150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}, I_E=0$	80			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=30\text{mA}, I_B=0$	80			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu\text{A}, I_C=0$	6			V
Collector cut-off current	I_{CBO}	$V_{CB}=80\text{V}, I_E=0$			100	μA
Collector cut-off current	I_{CEO}	$V_{CE}=60\text{V}, I_B=0$			100	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=6\text{V}, I_C=0$			100	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=4\text{V}, I_C=1\text{A}$	70		320	
	$h_{FE(2)}$	$V_{CE}=4\text{V}, I_C=3\text{A}$	10			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=3\text{A}, I_B=0.375\text{A}$			1.2	V
Base-emitter voltage	V_{BE}	$V_{CE}=4\text{V}, I_C=3\text{A}$			1.8	V
Transition frequency	f_T	$V_{CE}=5\text{V}, I_C=0.2\text{A}, f=10\text{MHz}$		30		MHz

CLASSIFICATION OF $h_{FE(1)}$

RANK	Q	P	O
RANGE	70-150	120-250	160-320